

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

Inventor(s): MIYASHITA et al.

Filed: Herewith

Title: SEMICONDUCTOR DEVICE COMPRISING METAL SILICIDE FILMS FORMED TO COVER GATE ELECTRODE AND SOURCE-DRAIN DIFFUSION LAYERS AND METHOD OF MANUFACTURING THE SAME

July 30, 2001

PRELIMINARY AMENDMENT

Hon. Commissioner of Patents
Washington, D.C. 20231

RECEIVED
U.S. PATENT AND TRADEMARK OFFICE
JULY 30 2001
SIR:

Please amend this application as follows:

IN THE SPECIFICATION:

At the top of the first page, just under the title, insert:

1. --This is a Continuation-In-Part Divisional
 Continuation Substitute Application (MPEP 201.09) of
1(a) National Application No. 09/164,343 filed October 1, 1998.
1(b) International Application No. PCT/_/
filed __ which designated the U.S.--

2. --This application claims the benefit of U.S. Provisional Application No. 60/___, filed ___.--

Respectfully submitted,

PILLSBURY WINTHROP LLP
Intellectual Property Group

By: Walter J. Deinode
for Attorney: Glenn J. Perry
Reg. No: 28,458
Tel. No.: 703-905-2161
Fax No.: 703-905-2500

Atty\Sec. GJP/WSE/dae
1600 Tysons Boulevard
McLean, VA 22102
(703) 905-2000